

ZP1350-RECTIFIER DIODE

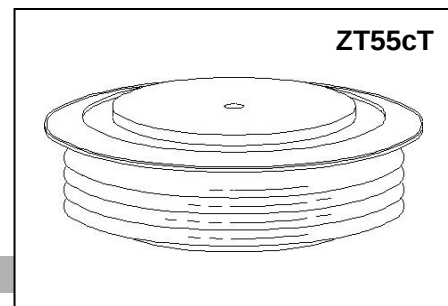
Shanghai Sunco Electronics Co., Ltd.

2500-3500V_{RRM}

GENERAL PURPOSE HIGH POWER STANDARD RECTIFIER

Features:

- . All Diffused Structure
- . High Surge rating
- . Blocking capability up to 3500 volts
- . Ceramic Housing Hermetic Package
- . Pressure Assembled Device



ELECTRICAL CHARACTERISTICS AND RATINGS

Reverse Blocking

Device Type	V _{RRM} (1)	V _{RSM} (1)
ZP1350-25	2500	2700
ZP1350-26	2600	2800
ZP1350-28	2800	3000
ZP1350-30	3000	3200
ZP1350-32	3200	3400
ZP1350-35	3500	3700

V_{RRM} = Repetitive peak reverse voltage

V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage	I _{RRM}	5 mA 50 mA (3)
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Notes:

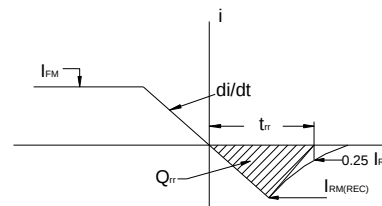
All ratings are specified for T_j=25 °C unless otherwise stated.

(1) All voltage ratings are specified for an applied 50Hz/60Hz sinusoidal waveform over the temperature range 0 to +150 °C.

(2) 10 msec. max. pulse width

(3) Maximum value for T_j = 150 °C.

(4) See parameter definition below :



REVERSE RECOVERY CHARACTERIST

Conducting - on state

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Average value of on-state current	I _{F(AV)}		1350		A	Sinewave, T _c =90 °C
RMS value of on-state current	I _{FRMS}		2119		A	Nominal value
Peak one cycle surge (non repetitive) current	I _{FSM}		18900		A	10 msec (50Hz), sinusoidal wave-shape, 180° conduction, T _j = 150 °C
I square t	I ² t		1.7 × 10 ⁶		A ² s	10 msec
Peak on-state voltage	V _{FM}		1.60		V	I _{FM} = 3000A; T _j =25°C
Threshold voltage	V _{FO}		0.88		V	T _j =150°C, I=0.5 π I _{F(AV)} to 1.5 π I _{F(AV)}
Slope resistance	r _F		0.20		mΩ	T _j =150°C, I=0.5 π I _{F(AV)} to 1.5 π I _{F(AV)}
Reverse Recovery Current (4)	I _{RM(REC)}				A	I _{FM} = 500 A; di/dt = -10 A/s; T _j max
Reverse Recovery Charge (4)	Q _{rr}			4500	μC	I _{FM} = 500 A; di/dt = -10 A/s; T _j max
Reverse Recovery Time (4)	t _{rr}				μs	I _{FM} = 500 A; di/dt = -10 A/s; T _j max

THERMAL AND MECHANICAL CHARACTERISTICS**ZP1350-Rectifier Diode**

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Operating temperature	T_j	-40	+150		°C	
Storage temperature	T_{stg}	-40	+150		°C	
Thermal resistance - junction to case	$R_{\theta(j-c)}$		0.022		°C/W	Double sided cooled
Thermal resistance - case to heatsink	$R_{\theta(c-s)}$		0.005		°C/W	Double sided cooled
Mounting force	P	22	27	25	kN	
Weight	W			0.46	kg.	

* Mounting surfaces smooth, flat and greaseless

CASE OUTLINE AND DIMENSIONS